

IN THE SPECIFICATION

Please amend the paragraph bridging pages 6 and 7 as follows:

Now, the wafer is subjected to a laser annealing process 30. A Nd:YAG laser may be used, having a wavelength of 1.06 nm and energy of between about 0.5 and 1.5 Joules/cm². Preferably, a KrF Excimer laser is used, having a wavelength of 248 nm and energy of between about 0.1 and 1.2 Joules/cm². A prior art approach uses very high laser energy to melt the silicon. In the process of the present invention, a solid state reaction process is used. The laser energy must be adjusted carefully so as not to cause melting of the silicon. It is possible that C40 titanium disilicide could be formed by another process, such as RTA. However, the laser annealing process of the present invention has been proved experimentally. This annealing will form phase C40 titanium disilicide (TiSi₂) 32 over the gate electrode and over the source and drain regions, as shown in Fig. 3. C40 titanium disilicide has a crystal lattice structure very similar to that of C54, but quite different from that of C49. The extreme non-equilibrium of the laser annealing process of the invention favors the formation of meta-stable phase C40 TiSi₂.